

T2800D



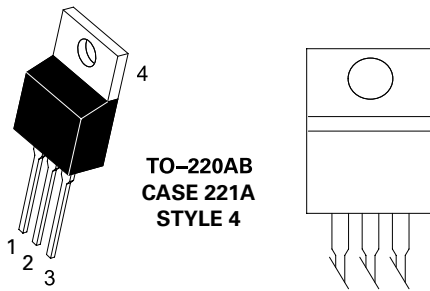
Description

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

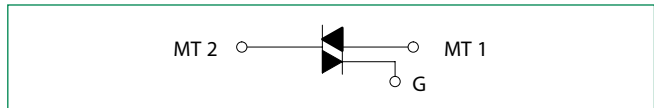
Features

- Blocking Voltage to 400 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Four Quadrant Gating
- Pb-Free Package is Available

Pin Out



Functional Diagram



Additional Information

Datasheet

Resources

Samples

Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Sine Wave 50 to 60 Hz, $T_J = -40$ to $+100^\circ\text{C}$, Gate Open)	V_{DRM} V_{RRM}	400	V
On-State RMS Current (All Conduction Angles, $T_C = +80^\circ\text{C}$)	$I_{\text{T (RMS)}}$	6.0	A
Peak Non-Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, $T_J = +80^\circ\text{C}$)	I_{TSM}	100	A
Circuit Fusing Considerations ($t = 8.3$ ms)	I^2t	40	A2s
Peak Gate Power (Pulse Width = 10 μsec , $T_C = +80^\circ\text{C}$)	P_{GM}	16	W
Average Gate Power ($t = 8.3$ msec, $T_C = +80^\circ\text{C}$)	$P_{\text{GM (AV)}}$	0.35	W
Peak Gate Current (Pulse Width = 10 μsec , $T_C = +80^\circ\text{C}$)	I_{GM}	4.0	A
Operating Junction Temperature Range @ Rated V_{RRM} and V_{DRM}	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta\text{JC}}$	2.2	$^\circ\text{C/W}$
Maximum Device Temperature for Soldering Purposes for 10 Sec	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Electrical Characteristics - OFF ($T_J = 25^\circ\text{C}$ unless otherwise noted ; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit	
Peak Repetitive Blocking Current ($V_D = V_{\text{DRM}} = V_{\text{RRM}}$; Gate Open)	I_{DRM} I_{RRM}	$T_J = 25^\circ\text{C}$	-	-	1.0	mA
		$T_J = 125^\circ\text{C}$	-	-	2.0	

Electrical Characteristics - ON ($T_J = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit	
Peak Forward On-State Voltage (Note 3) ($I_{\text{TM}} = \pm 30$ A)	V_{TM}	-	1.7	2.0	V	
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 100$ Ω)	I_{GT}	MT2(+), G(+)	-	10	25	mA
		MT2(+), G(-)	-	20	60	
		MT2(-), G(-)	-	15	25	
		MT2(-), G(+)	-	30	60	
Gate Trigger Voltage (Continuous dc) (All Four Quadrants) ($V_D = 12$ Vdc, $R_L = 100$ Ω)	V_{GT}	-	1.25	2.5	V	
Gate Non-Trigger Voltage (Continuous dc) ($V_D = 12$ Vdc, $R_L = 100$ Ω , $T_C = 100^\circ\text{C}$)	V_{GD}	0.2	-	-	V	
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current) = ± 200 mA)	I_{H}	-	15	30	mA	
Gate Controlled Turn-On Time (Rated V_{DRM} , $I_T = 10$ A, $I_{\text{GT}} = 160$ mA, Rise Time = 0.1 μs)	t_{gt}	-	1.6	-	μs	

Dynamic Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Critical Rate-of-Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{T(RMS)} = 8 \text{ A}$, Commutating $di/dt = 4.1 \text{ A/ms}$, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$(di/dt)_c$	-	10	-	A/ms
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Voltage Rise, Gate Open, $T_C = 100^\circ\text{C}$)	dv/dt	60	-	-	V/ μs

2. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

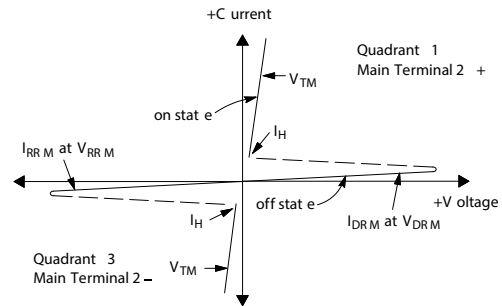


Figure 1. Current Derating

Quadrant Definitions for a Triac

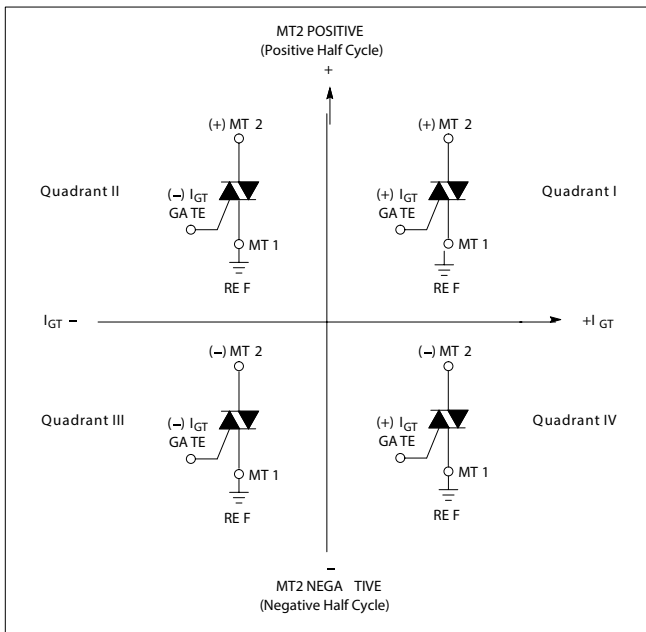
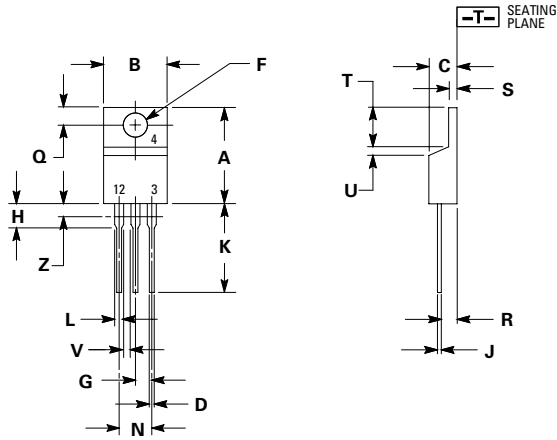


Figure 2. Power Dissipation

All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used

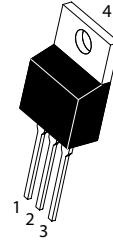
Dimensions



Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.590	0.620	14.99	15.75
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
H	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

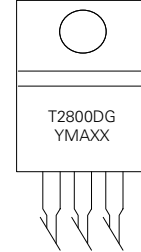
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Part Marking System



**TO-220AB
CASE 221A
STYLE 12**

x =D, M, or N
Y =Year
M =Month
A =Assembly Site
XX =Lot Serial Code
G =Pb-Free Package



Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	No Connection

Ordering Information

Device	Package	Shipping
T2800D	TO-220AB	500 Units/ Box
T2800DG	TO-220AB (Pb-Free)	

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at <http://www.littelfuse.com/disclaimer-electronics>.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Littelfuse\(美国力特\)](#)